



**Central**<sup>TM</sup>  
Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMHSH-3 type is a Silicon Schottky diode, epoxy molded in a SOD-123 surface mount package, designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: CH3**

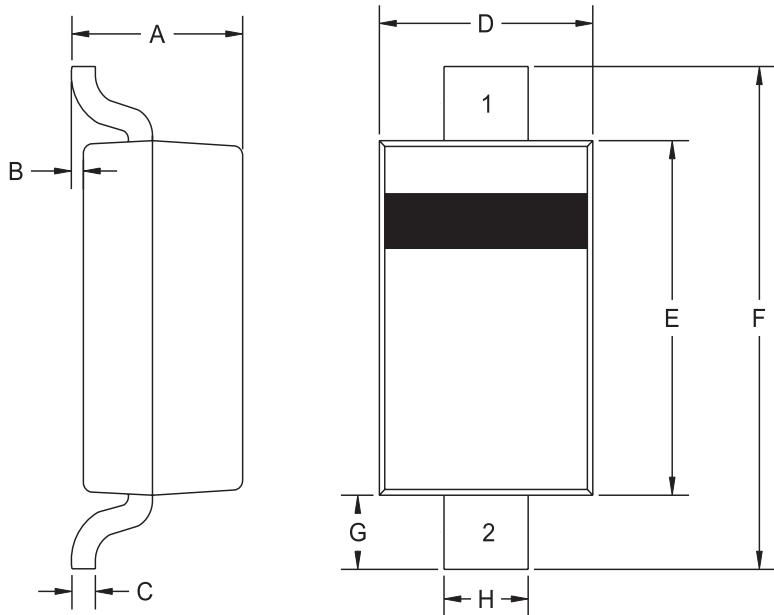
**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

	<b>SYMBOL</b>	<b>UNITS</b>
Peak Repetitive Reverse Voltage	$V_{RRM}$	V
Continuous Forward Current	$I_F$	mA
Peak Repetitive Forward Current	$I_{FRM}$	mA
Forward Surge Current, $t_p < 1.0\text{s}$	$I_{FSM}$	mA
Power Dissipation	$P_D$	mW
Junction and Storage Temperature	$T_J, T_{stg}$	${}^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	${}^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
$I_R$	$V_R=25\text{V}$			2.0	$\mu\text{A}$
$V_{BR}$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=100\mu\text{A}$			240	$\text{mV}$
$V_F$	$I_F=1.0\text{mA}$			320	$\text{mV}$
$V_F$	$I_F=10\text{mA}$			400	$\text{mV}$
$V_F$	$I_F=30\text{mA}$			500	$\text{mV}$
$V_F$	$I_F=100\text{mA}$			1000	$\text{mV}$
$C_T$	$V_R=1.0\text{V}, f=1\text{ MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, R_L=100\Omega$ , Rec. to 1.0mA		7.0		ns

SOD-123 CASE - MECHANICAL OUTLINE



R4

**LEAD CODE:**

- 1) CATHODE
- 2) ANODE

**MARKING CODE: CH3**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	0.000	0.005	0.00	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.110	2.50	2.80
F	0.142	0.154	3.60	3.90
G	0.016	-	0.40	-
H	0.020	0.028	0.50	0.70

SOD-123 (REV:R4)

R4 (26-April 2005)